

Notice of References Cited	Application/Control No. 10/505,219	Applicant(s)/Patent Under Reexamination HOSONO ET AL.	
	Examiner Matthew W. Such	Art Unit 2891	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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	C	US-			
	D	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*	V	Ueda, K., et al. "Transparent p-type Semiconductor: LaCuOS Layered Oxysulfide." APPL. PHYS. LETT. Vol. 77 (2000): pp. 2701-2703.
*	W	Ueda, K., et al. "Room-Temperature Excitons in Wide-Gap Layered-Oxysulfide Semiconductor: LaCuOS." APPL. PHYS. LETT. Vol. 78 (2001): pp. 2333-2335.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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